

# TLP361J

- Triac Drivers
- Programmable Controllers
- AC-Output Modules
- Solid State Relays

The TOSHIBA TLP361J consists of a zero-voltage-crossing turn-on photo-triac optically coupled to a gallium arsenide infrared-emitting diode in a four-lead plastic DIP package.

- Peak off-state voltage: 600 V (Min.)
- Trigger LED current: 10 mA (Max.)
- On-state current: 100 mA (Max.)
- Isolation voltage: 5000 Vrms (Min.)
- Zero crossing Function
- UL recognized: UL1577, file No. E67349
- Option (D4) type  
TÜV approved: DIN EN60747-5-2

Certificate No. R50033433

Maximum operating insulation voltage : 890 Vpk

Maximum permissible overvoltage : 8000 Vpk

(Note) When an EN60747-5-2 approved type is needed, please designate "Option (D4)."

•Construction mechanical rating

	7.62 mm pitch TLPXXX type	10.16 mm pitch TLPXXX type
Creepage distance	7.0 mm (min)	8.0 mm (min)
Clearance	7.0 mm (min)	8.0 mm (min)
Insulation thickness	0.4 mm (min)	0.4 mm (min)

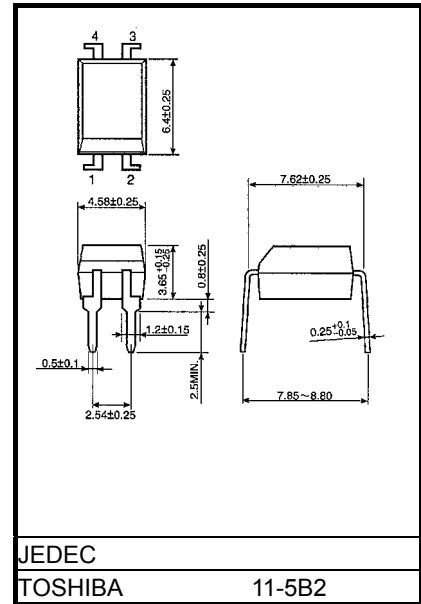
•Trigger LED current

Classi- fication*	Trigger LED current (mA)		Marking of classification
	V <sub>T</sub> =3V, T <sub>a</sub> =25°C		
	Min.	Max.	
(IFT7)		7	T7
Standard	—	10	T7, blank

\*Example: "(IFT7)"; "TLP361J(IFT7)"

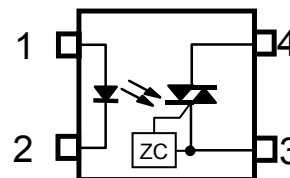
(Note) When specifying the application type name for certification testing, be sure to use the standard product type name, e.g., TLP361J(IFT7): TLP361J

Unit: mm



Weight: 0.26 g (Typ.)

Pin configuration (top view)



- 1: Anode
- 2: Cathode
- 3: Terminal1
- 4: Terminal2

## Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
LED	Forward current	$I_F$	50	mA
	Forward current derating (Ta ≥ 53°C)	$\Delta I_F / ^\circ\text{C}$	-0.7	mA / °C
	Peak forward current (100 μs pulse, 100 pps)	$I_{FP}$	1	A
	Reverse voltage	$V_R$	5	V
	Junction temperature	$T_j$	125	°C
Detector	Off-state output terminal voltage	$V_{DRM}$	600	V
	On-state RMS current	Ta = 25°C	100	mA
		Ta = 70°C	50	
	On-state current derating (Ta ≥ 25°C)	$\Delta I_T / ^\circ\text{C}$	-1.1	mA / °C
	Peak on-state current (100 μs pulse, 120 pps)	$I_{TP}$	2	A
	Peak nonrepetitive surge current (Pw = 10 ms, DC = 10%)	$I_{TSM}$	1.2	A
	Junction temperature	$T_j$	115	°C
Storage temperature range	$T_{stg}$	-55~125	°C	
Operating temperature range	$T_{opr}$	-40~100	°C	
Lead soldering temperature (10s)	$T_{sol}$	260	°C	
Isolation voltage (AC, 1 min., R.H. ≤ 60%)	(Note 1) $BV_S$	5000	Vrms	

(Note 1): Pins 1 and 2 are shorted together and pins 3 and 4 are shorted together.

## Recommended Operating Conditions

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	$V_{AC}$	—	—	240	$V_{ac}$
Forward current	$I_F$	15	20	25	mA
Peak on-state current	$I_{TP}$	—	—	1	A
Operating temperature	$T_{opr}$	-25	—	85	°C

Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

**Electrical Characteristics (Ta = 25°C)**

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
LED	Forward voltage	$V_F$	$I_F = 10 \text{ mA}$	1.0	1.15	1.3	V
	Reverse current	$I_R$	$V_R = 5 \text{ V}$	—	—	10	$\mu\text{A}$
	Capacitance	$C_T$	$V = 0, f = 1 \text{ MHz}$	—	30	—	pF
Detector	Peak off-state current	$I_{DRM}$	$V_{DRM} = 600 \text{ V}$	—	10	1000	nA
	Peak on-state voltage	$V_{TM}$	$I_{TM} = 100 \text{ mA}$	—	1.7	3.0	V
	Holding current	$I_H$	—	—	0.6	—	mA
	Critical rate of rise of off-state voltage	dv/dt	$V_{in} = 240 \text{ Vrms}, T_a = 85^\circ\text{C}$ (Note 2)	200	500	—	V/ $\mu\text{s}$
	Critical rate of rise of commutating voltage	dv/dt(c)	$V_{in} = 60 \text{ Vrms}, I_T = 1.5 \text{ mA}$ (Note 2)	—	0.2	—	V/ $\mu\text{s}$

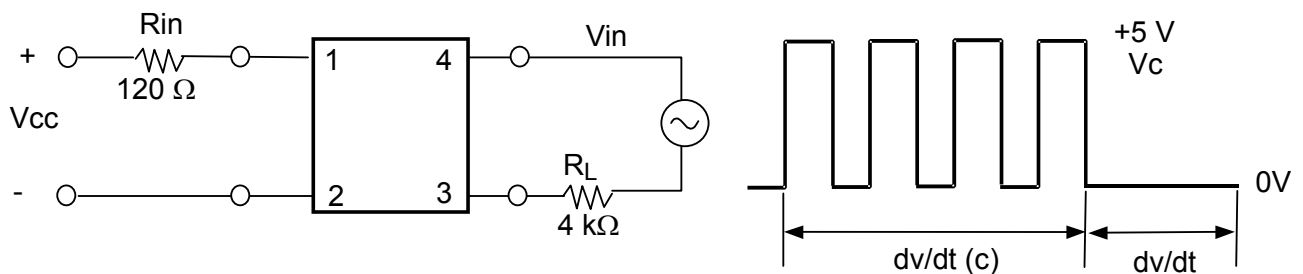
**Coupled Electrical Characteristics (Ta = 25°C)**

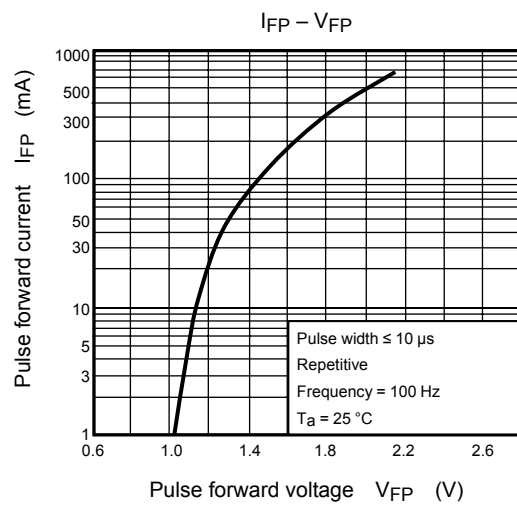
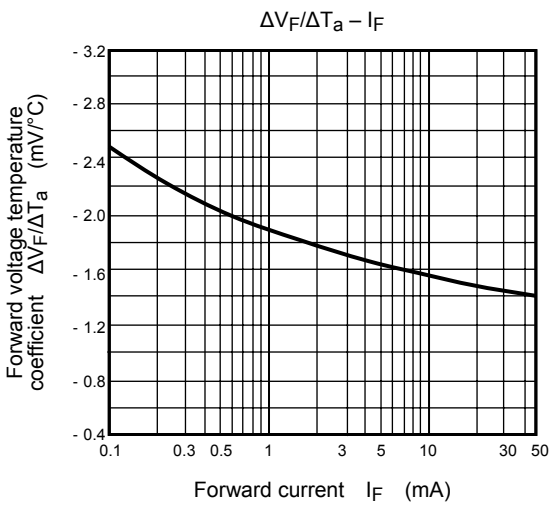
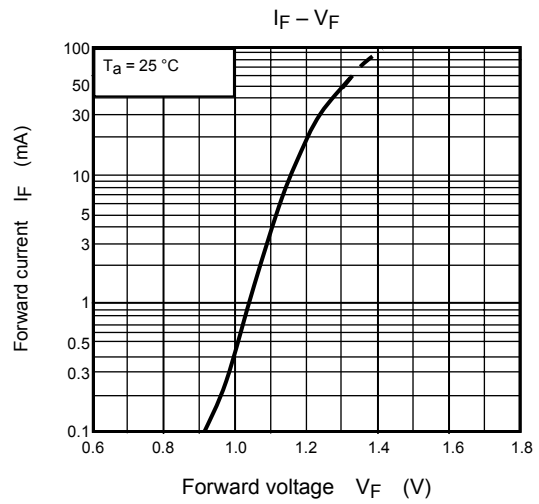
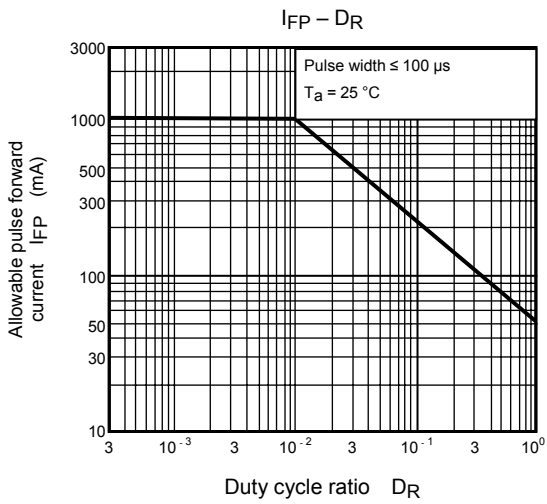
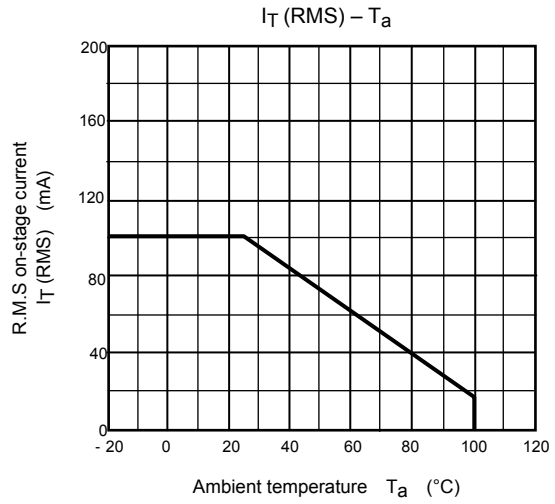
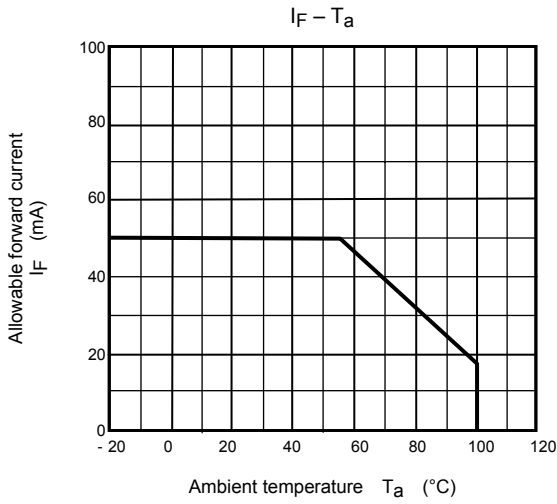
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Trigger LED current	$I_{FT}$	$V_T = 3 \text{ V}$	—	—	10	mA
Inhibit voltage	$V_{IH}$	$I_F = \text{Rated } I_{FT}$	—	—	20	V
Leakage in inhibited state	$I_{IH}$	$I_F = \text{Rated } I_{FT}$ $V_T = \text{Rated } V_{DRM}$	—	200	600	$\mu\text{A}$
Turn-on time	$t_{ON}$	$V_D = 3 \rightarrow 1.5 \text{ V}, R_L = 20 \Omega$ $I_F = \text{Rated } I_{FT} \times 1.5$	—	30	100	$\mu\text{s}$

**Isolation Characteristics (Ta = 25°C)**

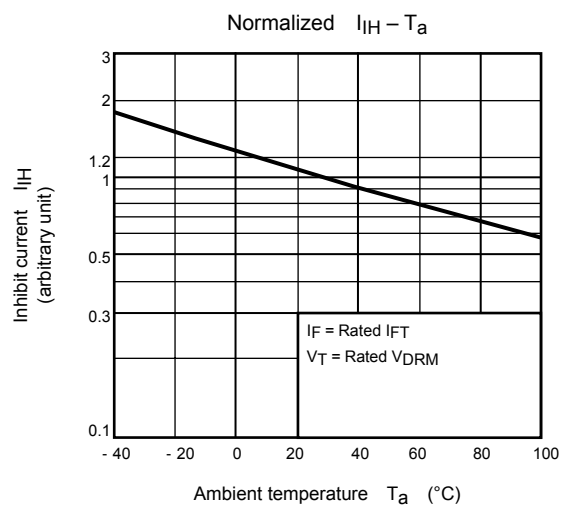
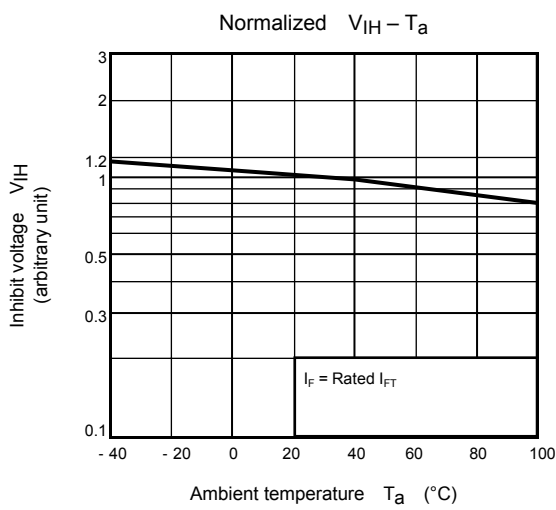
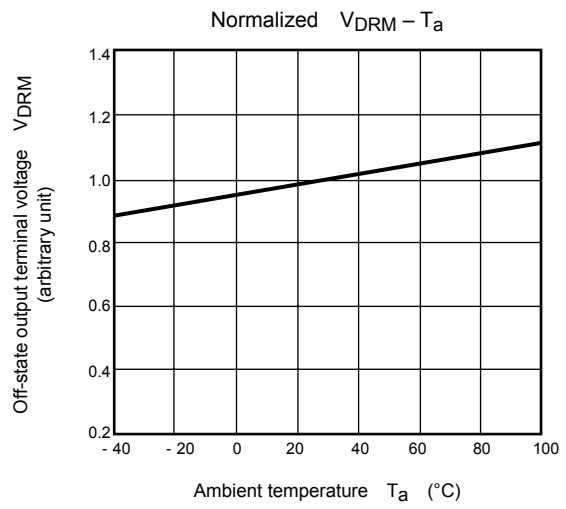
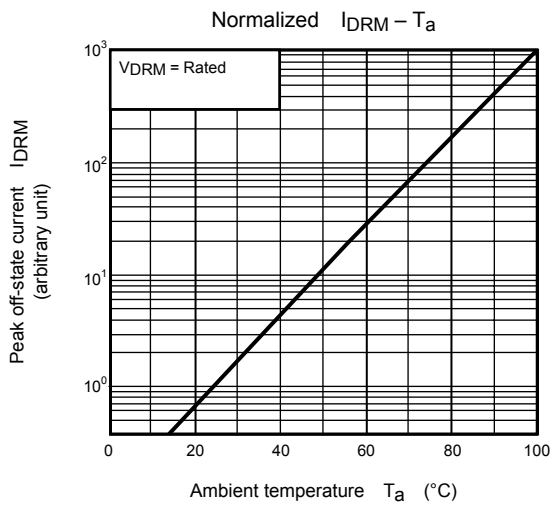
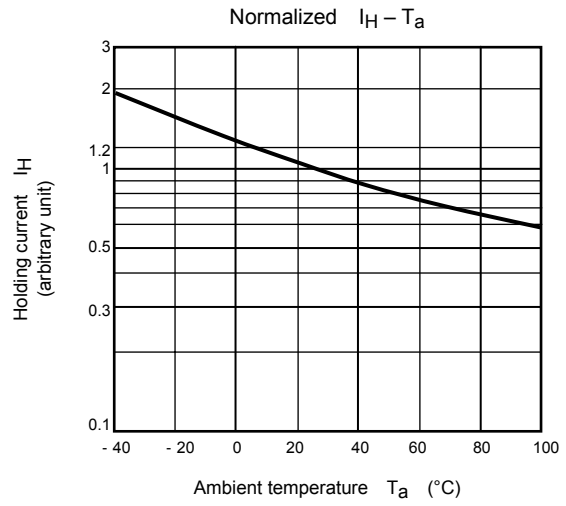
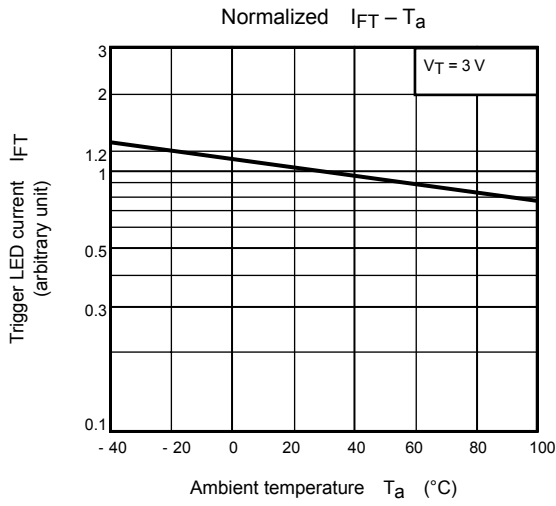
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Capacitance (input to output)	$C_S$	$V_S = 0, f = 1 \text{ MHz}$	—	0.8	—	pF
Isolation resistance	$R_S$	$V_S = 500 \text{ V}, \text{R.H.} \leq 60\%$	$1 \times 10^{12}$	$10^{14}$	—	$\Omega$
Isolation voltage	$BV_S$	AC, 1 minute	5000	—	—	Vrms
		AC, 1 second, in oil	—	10000	—	Vrms
		DC, 1 minute, in oil	—	10000	—	Vdc

(Note 2): dv/dt test circuit





\*: The above graphs show typical characteristics.



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